

Fig. 1 is a cross-sectional view of a semiconductor device. The device is built on a substrate 10, which is divided into an n⁺ region (10) and a p⁺ region (13). A layer 11 is formed on the n⁺ region 10. A layer 12 is formed on the p⁺ region 13. A layer 13 is formed on the n⁺ region 10. A layer 14 is formed on the p⁺ region 13. A layer 21 is formed on the n⁺ region 10. A layer 22 is formed on the p⁺ region 13. A layer 23 is formed on the n⁺ region 10. A layer 231 is formed on the p⁺ region 13. A layer 31 is formed on the n⁺ region 10. A layer 32 is formed on the p⁺ region 13. A layer 33 is formed on the n⁺ region 10.